COMPLEMENTARY PAIR ENHANCEMENT MODE MOSFET

Product Summary

Device	BV_{DSS}	$R_{DS(ON)}$	I_D T_A = +25°C
Q1	30V	460mΩ @ V_{GS} = 4.5V	1.1A
		560mΩ @ V_{GS} = 2.5V	1.0A
Q2	-30V	1000mΩ @ V_{GS} = -4.5V	-0.7A
		1500mΩ @ V_{GS} = -2.5V	-0.6A

Features and Benefits

- Low On-Resistance
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **An automotive-compliant part is available under separate datasheet (DMC3732UVTQ)**

Description

This new generation MOSFET is designed to minimize the on-state resistance ($R_{DS(ON)}$) yet maintain superior switching performance, making it ideal for high-efficiency power-management applications.

Mechanical Data

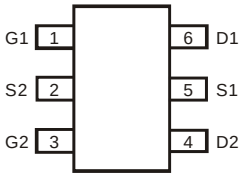
- Package: TSOT26
- Package Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals Connections: See Diagram
- Terminals: Finish – Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 e3
- Weight: 0.013 grams (Approximate)

Applications

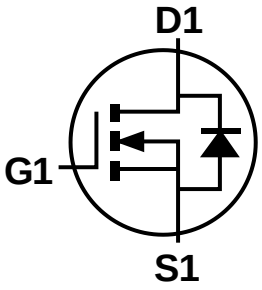
- Backlighting
- DC-DC converters
- Power-management functions

TSOT26

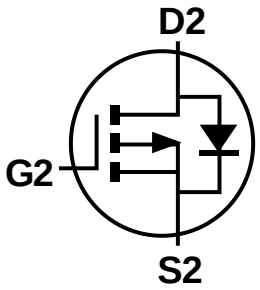
Top View



Top View



Q1 N-Channel



Q2 P-Channel

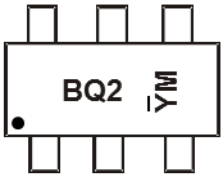
Ordering Information (Note 4)

Part Number	Package	Packing	
		Qty.	Carrier
DMC3732UVT-7	TSOT26	3,000	Tape & Reel
DMC3732UVT-13	TSOT26	10,000	Tape & Reel

Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

Marking Information

TSOT26



BQ2 = Product Type Marking Code
YM = Date Code Marking
Y = Year (ex: K = 2023)
M = Month (ex: 9 = September)

Date Code Key

Year	2022	2023	2024	2025	2026	2027	2028	2029	2030	2031	2032	2033
Code	J	K	L	M	N	P	R	S	T	U	V	W

Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D

Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic			Symbol	Q1 Value	Q2 Value	Unit
Drain-Source Voltage			V_{DSS}	30	-30	V
Gate-Source Voltage			V_{GSS}	±8	±8	V
Continuous Drain Current (Note 6) V_{GS} = 4.5V	Steady State	T_A = +25°C T_A = +70°C	I_D	1.1 0.9	-0.7 -0.6	A
Maximum Continuous Body Diode Forward Current (Note 6)			I_S	0.73	-0.68	A
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)			I_{DM}	2.6	-1.9	A

Thermal Characteristics

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 5)	P_D	0.54	W
Thermal Resistance, Junction to Ambient @T_A = +25°C (Note 5)	$R_{\theta JA}$	230	°C/W
Power Dissipation (Note 6)	P_D	0.83	W
Thermal Resistance, Junction to Ambient @T_A = +25°C (Note 6)	$R_{\theta JA}$	150	°C/W
Operating and Storage Temperature Range	T_J, T_{STG}	-55 to +150	°C

Electrical Characteristics – Q1 N-Channel (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 8)						
Drain-Source Breakdown Voltage	BV_{DSS}	30	—	—	V	V_{GS} = 0V, I_D = 10µA
Zero Gate Voltage Drain Current	I_{DSS}	—	—	1	µA	V_{DS} = 30V, V_{GS} = 0V
Gate-Source Leakage	I_{GSS}	—	—	±10	µA	V_{GS} = ±8V, V_{DS} = 0V
ON CHARACTERISTICS (Note 8)						
Gate Threshold Voltage	$V_{GS(TH)}$	0.45	—	0.95	V	V_{DS} = V_{GS}, I_D = 250µA
Static Drain-Source On-Resistance	$R_{DS(ON)}$	—	290 340 400	460 560 730	mΩ	V_{GS} = 4.5V, I_D = 200mA V_{GS} = 2.5V, I_D = 100mA V_{GS} = 1.8V, I_D = 75mA
Diode Forward Voltage	V_{SD}	—	0.6	1.2	V	V_{DS} = V_{GS}, I_D = 300mA
DYNAMIC CHARACTERISTICS (Note 9)						
Input Capacitance	C_{iss}	—	40.8	—	pF	V_{DS} = 25V, V_{GS} = 0V, f = 1.0MHz
Output Capacitance	C_{oss}	—	7.6	—		
Reverse Transfer Capacitance	C_{rss}	—	4.6	—		
Total Gate Charge	Q_g	—	0.9	—	nC	V_{GS} = 4.5V, V_{DS} = 15V, I_D = 1A
Gate-Source Charge	Q_{gs}	—	0.05	—		
Gate-Drain Charge	Q_{gd}	—	0.3	—		
Turn-On Delay Time	$t_{D(ON)}$	—	1.1	—	ns	V_{DS} = 10V, I_D = 1A V_{GS} = 4.5V, R_G = 6Ω
Turn-On Rise Time	t_R	—	15.9	—		
Turn-Off Delay Time	$t_{D(OFF)}$	—	20.7	—		
Turn-Off Fall Time	t_F	—	20.0	—		

Notes:
5. Device mounted on FR-4 substrate PCB, 2oz copper, with minimum recommended pad layout.
6. Device mounted on FR-4 substrate PCB, 2oz copper, with 1inch square copper plate.
7. Repetitive rating, pulse width limited by junction temperature.
8. Short duration pulse test used to minimize self-heating effect.
9. Guaranteed by design. Not subject to production testing.

Electrical Characteristics – Q2 P-Channel (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)						
Drain-Source Breakdown Voltage	BV_{DSS}	-30	—	—	V	V_{GS} = 0V, I_D = -250µA
Zero Gate Voltage Drain Current	I_{DSS}	—	—	-1	µA	V_{DS} = -30V, V_{GS} = 0V
Gate-Source Leakage	I_{GSS}	—	—	±10	µA	V_{GS} = ±8V, V_{DS} = 0V
ON CHARACTERISTICS (Note 7)						
Gate Threshold Voltage	$V_{GS(TH)}$	-0.5	—	-1.1	V	V_{DS} = V_{GS}, I_D = -250µA
Static Drain-Source On-Resistance	$R_{DS(ON)}$	—	0.72 0.86 1.0	1 1.5 2	Ω	V_{GS} = -4.5V, I_D = -400mA V_{GS} = -2.5V, I_D = -200mA V_{GS} = -1.8V, I_D = -100mA
Diode Forward Voltage	V_{SD}	—	-0.9	-1.2	V	V_{GS} = 0V, I_S = -300mA
DYNAMIC CHARACTERISTICS (Note 8)						
Input Capacitance	C_{iss}	—	54	—	pF	V_{DS} = -15V, V_{GS} = 0V f = 1.0MHz
Output Capacitance	C_{oss}	—	10.9	—		
Reverse Transfer Capacitance	C_{rss}	—	5.8	—		
Total Gate Charge	Q_g	—	1.0	—	nC	V_{GS} = -4.5V, V_{DS} = -15V, I_D = -1A
Total Gate Charge	Q_g	—	1.6	—		V_{GS} = -8V, V_{DS} = -15V I_D = -1A
Gate-Source Charge	Q_{gs}	—	0.2	—		
Gate-Drain Charge	Q_{gd}	—	0.1	—		
Turn-On Delay Time	$t_{D(ON)}$	—	3.8	—	ns	V_{DD} = -10V, R_L = 10Ω V_{GS} = -4.5V, R_G = 6Ω
Turn-On Rise Time	t_R	—	11	—		
Turn-Off Delay Time	$t_{D(OFF)}$	—	45	—		
Turn-Off Fall Time	t_F	—	20	—		

Notes: 7. Repetitive rating, pulse width limited by junction temperature.
8. Short duration pulse test used to minimize self-heating effect.

Q1 N-Channel

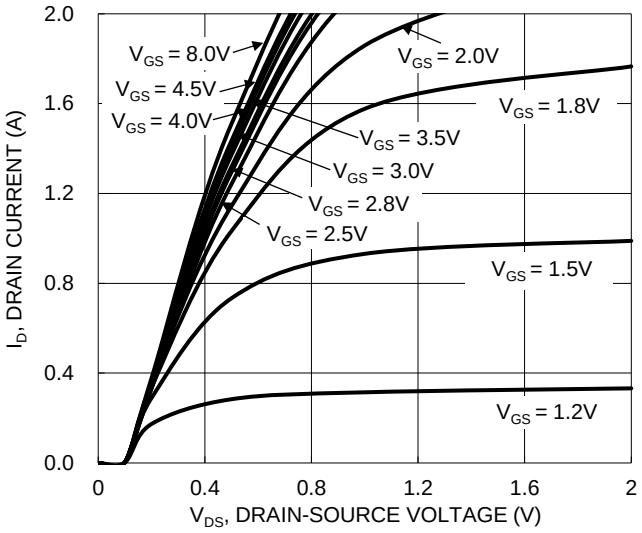


Figure 1. Typical Output Characteristic

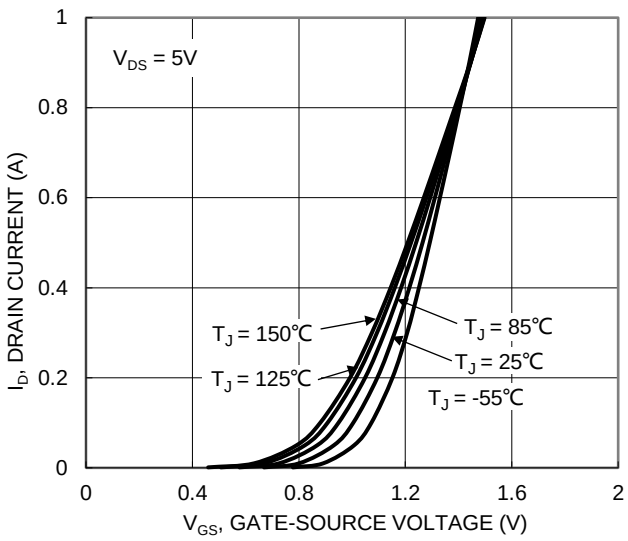


Figure 2. Typical Transfer Characteristic

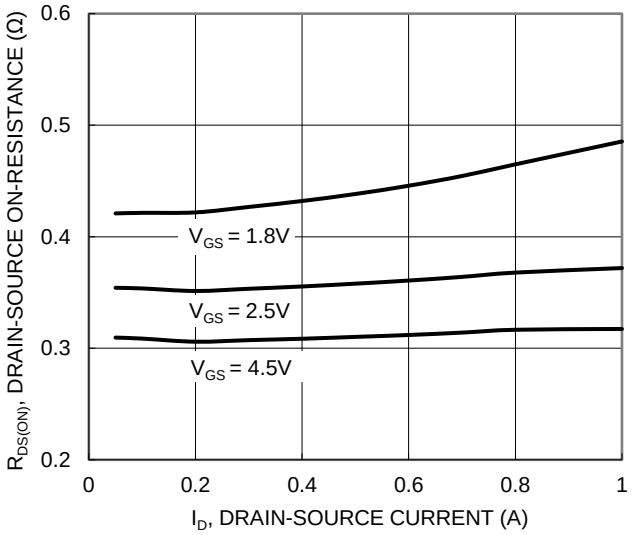


Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

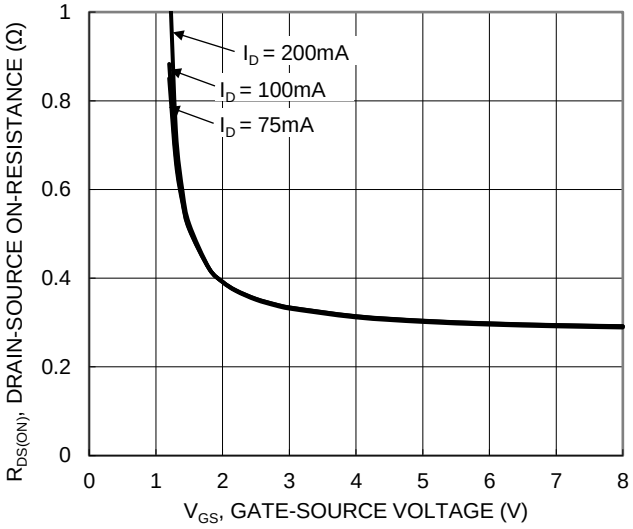


Figure 4. Typical Transfer Characteristic

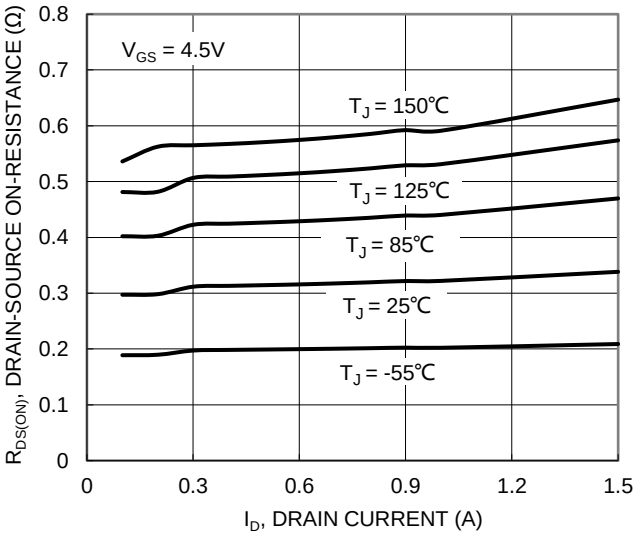


Figure 5. Typical On-Resistance vs. Drain Current and Junction Temperature

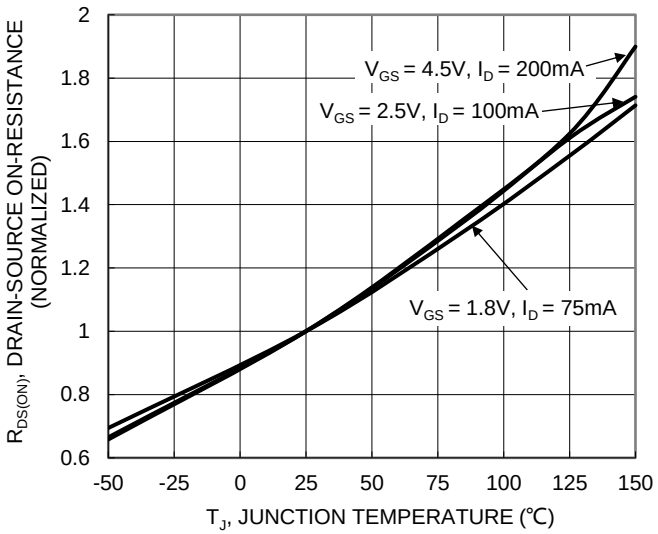


Figure 6. On-Resistance Variation with Junction Temperature

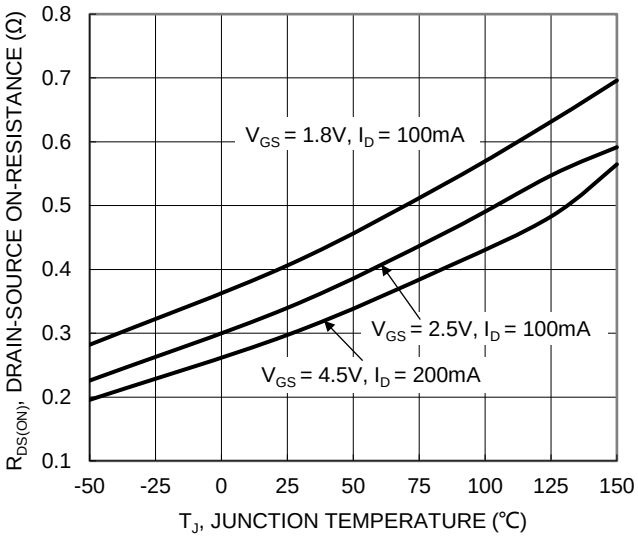


Figure 7. On-Resistance Variation with Junction Temperature

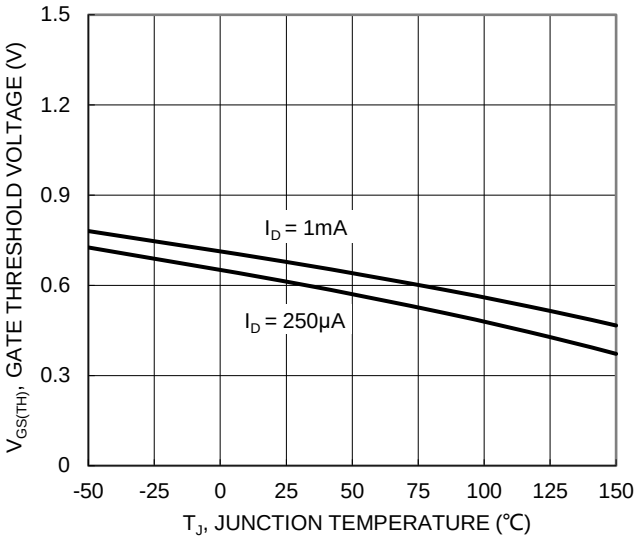


Figure 8. Gate Threshold Variation vs. Junction Temperature

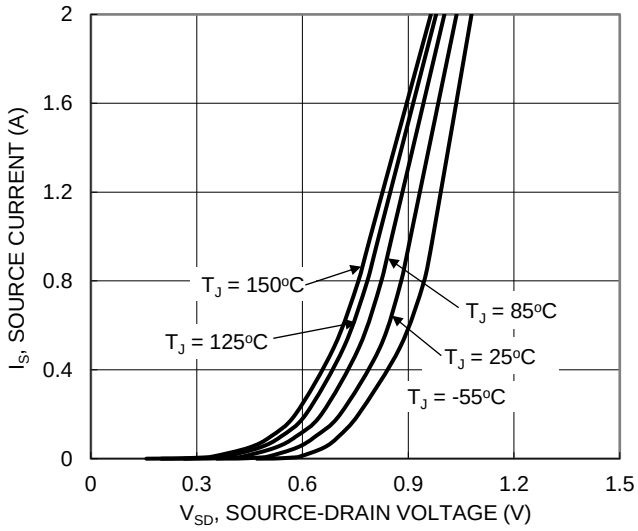


Figure 9. Diode Forward Voltage vs. Current

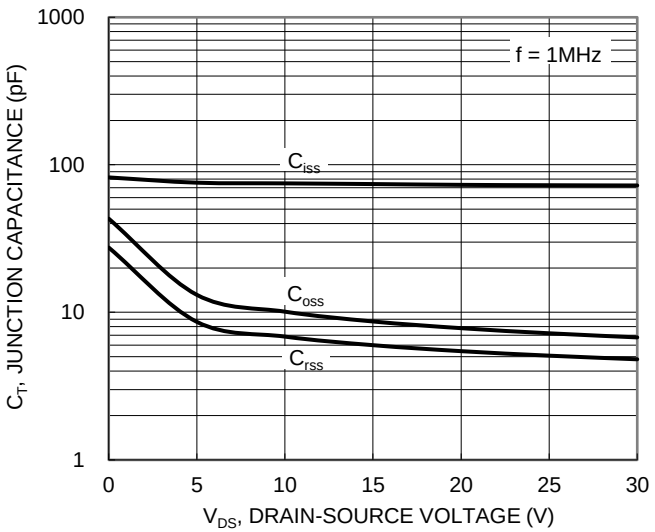


Figure 10. Typical Junction Capacitance

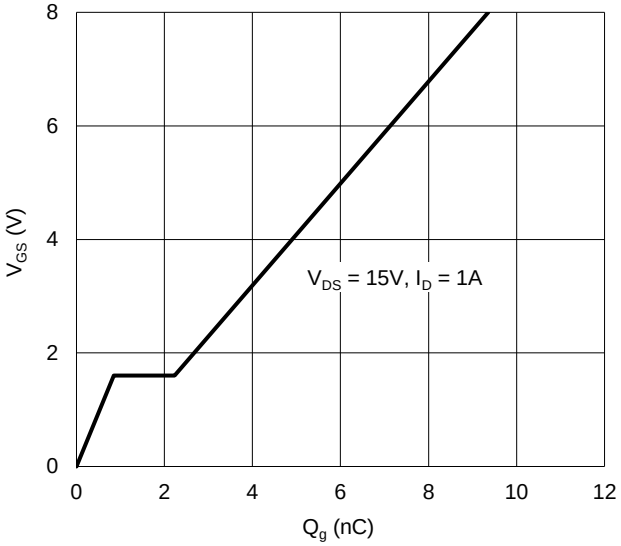


Figure 11. Gate Charge

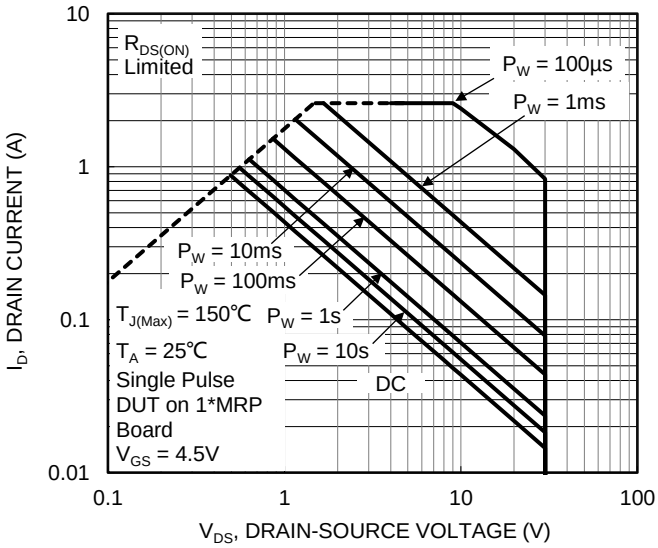


Figure 12. SOA, Safe Operation Area

Q2 P-Channel

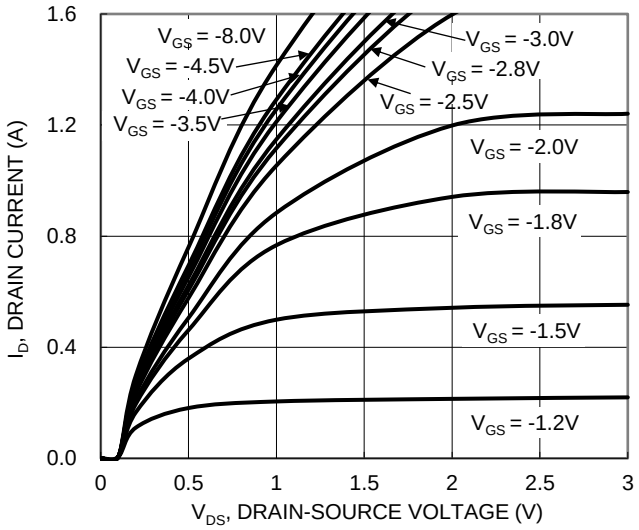


Figure 13. Typical Output Characteristic

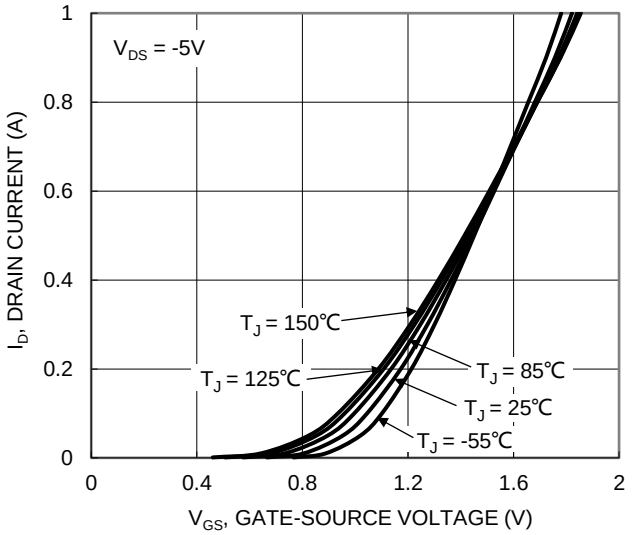


Figure 14. Typical Transfer Characteristic

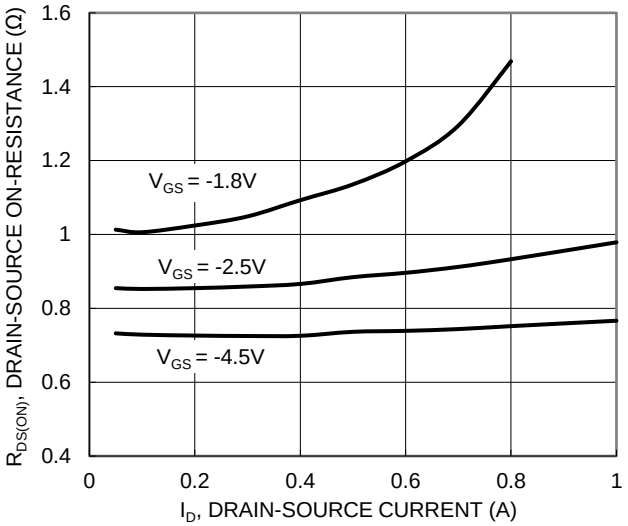


Figure 15. Typical On-Resistance vs. Drain Current and Gate Voltage

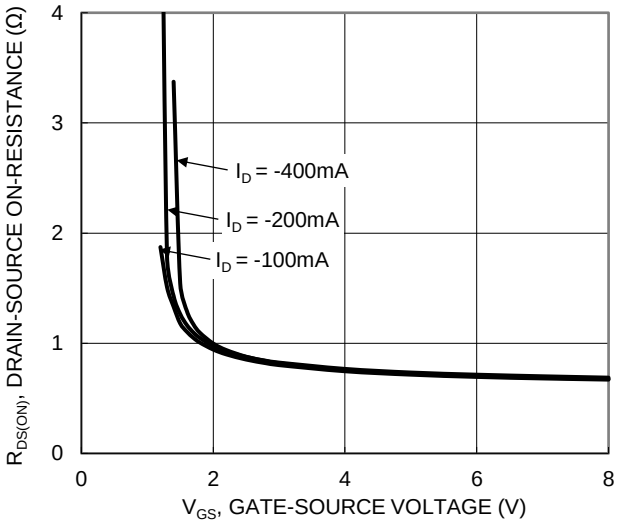


Figure 16. Typical Transfer Characteristic

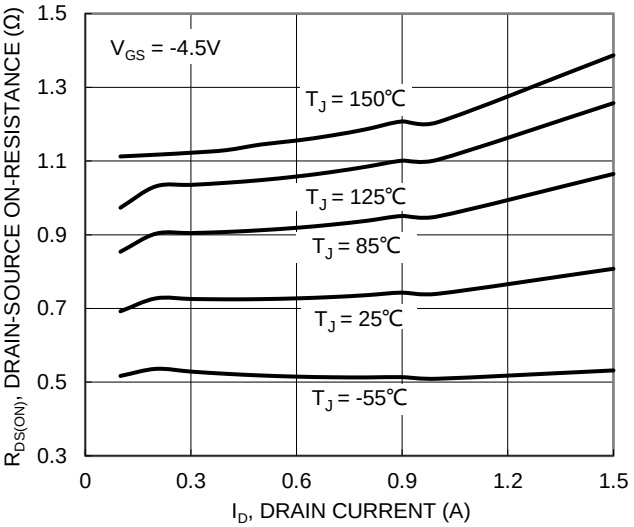


Figure 17. Typical On-Resistance vs. Drain Current and Junction Temperature

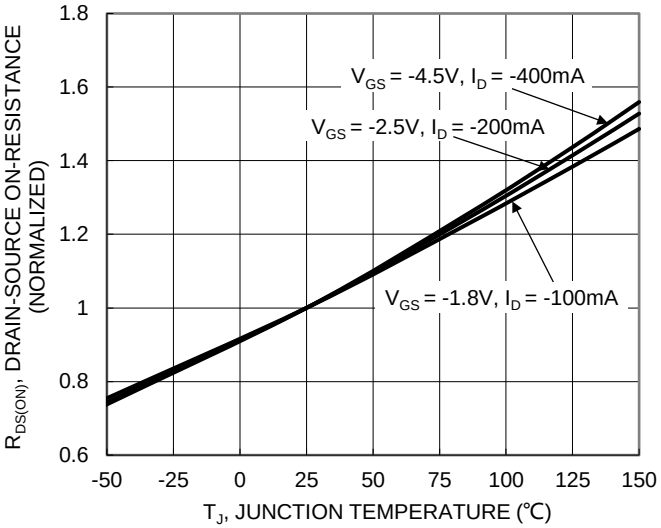


Figure 18. On-Resistance Variation with Junction Temperature

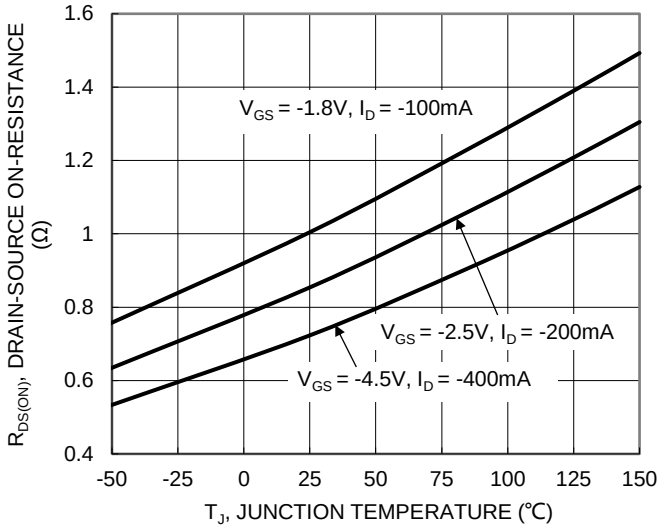


Figure 19. On-Resistance Variation with Junction Temperature

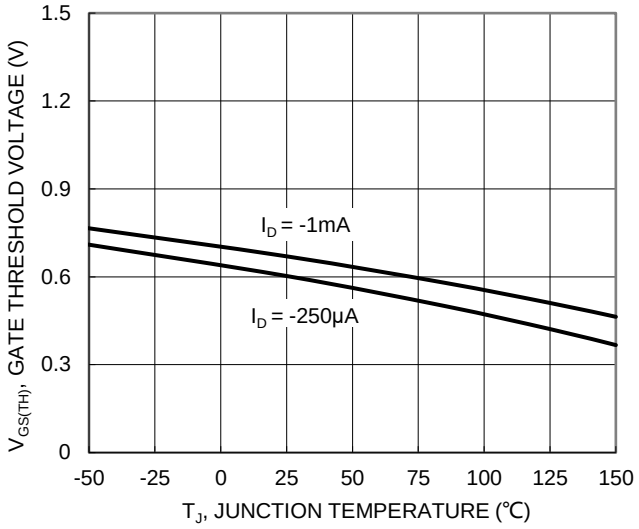


Figure 20. Gate Threshold Variation vs. Junction Temperature

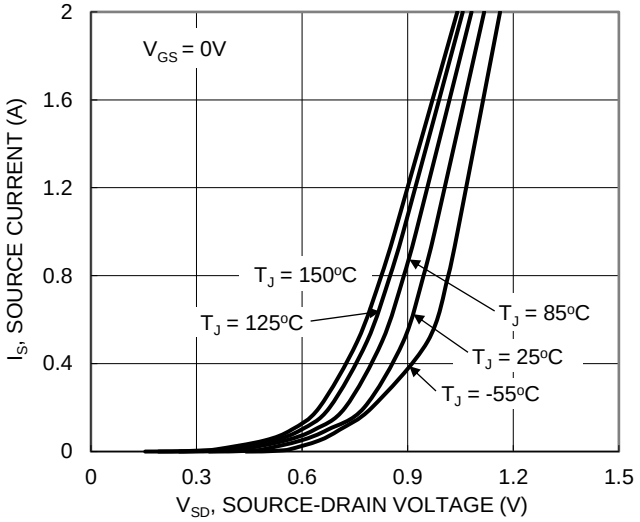


Figure 21. Diode Forward Voltage vs. Current

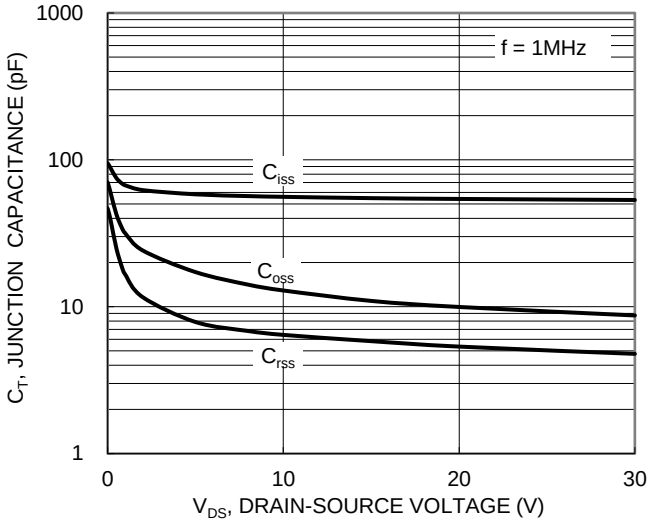


Figure 22. Typical Junction Capacitance

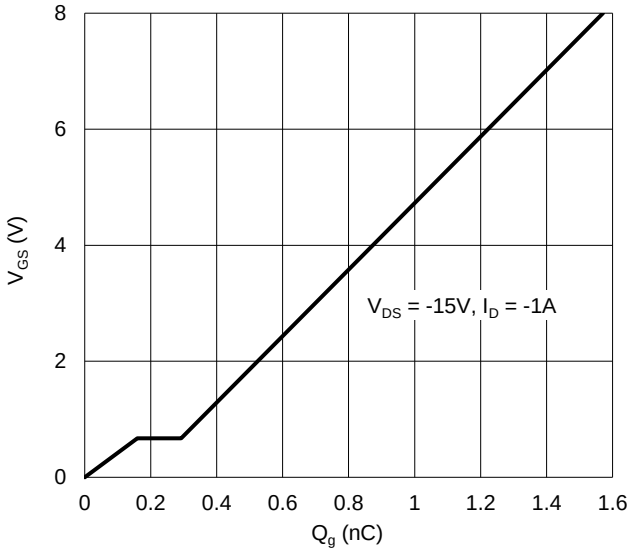


Figure 23. Gate Charge

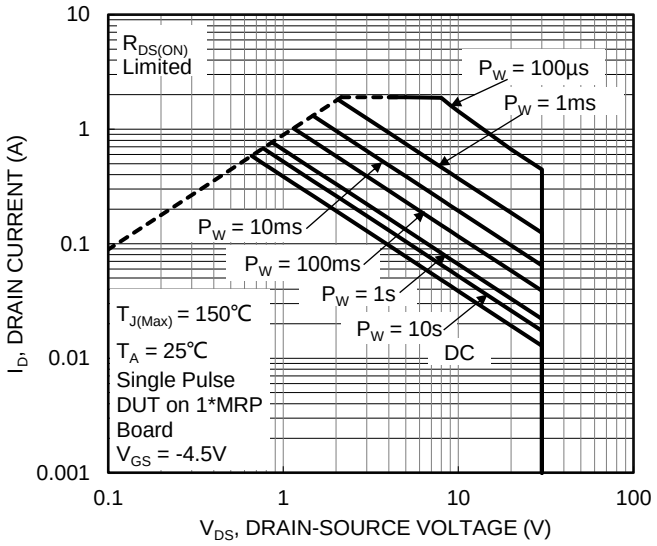


Figure 24. SOA, Safe Operation Area

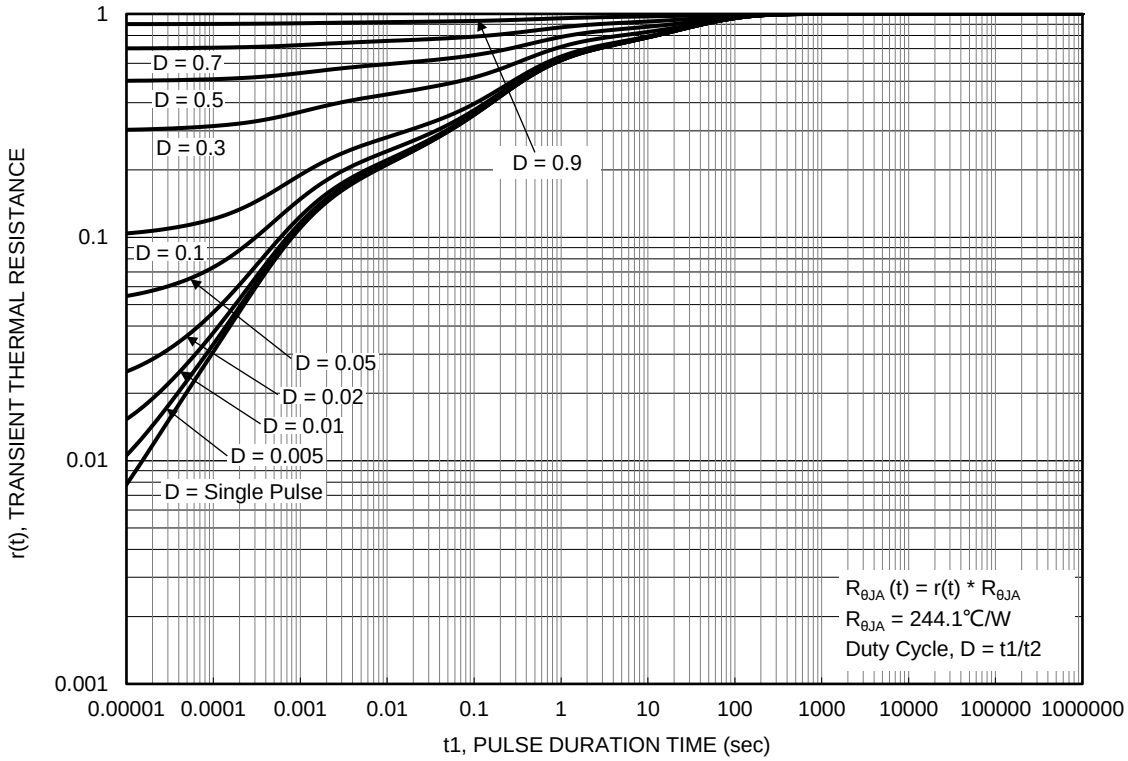
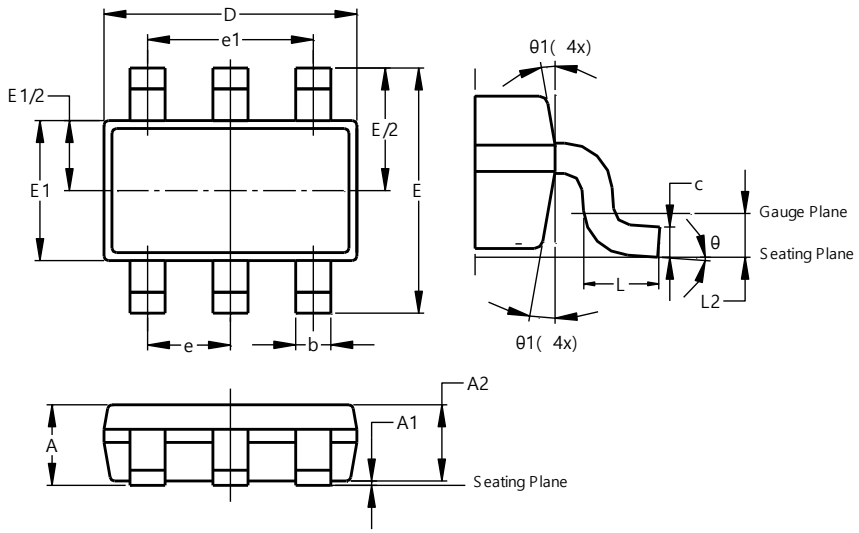


Figure 25. Transient Thermal Resistance

Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

TSOT26

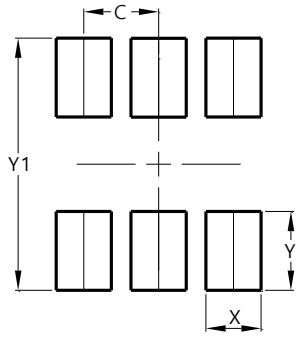


TSOT26			
Dim	**Min**	**Max**	**Typ**
A	–	1.00	–
A1	0.010	0.100	–
A2	0.840	0.900	–
D	2.800	3.000	2.900
E	2.800 BSC		
E1	1.500	1.700	1.600
b	0.300	0.450	–
c	0.120	0.200	–
e	0.950 BSC		
e1	1.900 BSC		
L	0.30	0.50	–
L2	0.250 BSC		
θ	0°	8°	4°
θ1	4°	12°	–
All Dimensions in mm			

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

TSOT26



Dimensions	Value (in mm)
C	0.950
X	0.700
Y	1.000
Y1	3.200

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